TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER MMIC AMPLIFIER TMD5872-2

FEATURES

- HIGH POWER
 P1dB=34.0dBm at 5.8GHz to 7.2GHz
- HIGH GAIN
 G1dB=29.0dB at 5.8GHz to 7.2GHz
- BROAD BAND INTERNALLY MATCHED
- HERMETICALLY SEALED PACKAGE

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD	V	15
Gate Supply Voltage	VGG	V	-10
Input Power	Pin	dBm	10
Flange Temperature	Tf	°C	-30 ~ + 80
Storage Temperature	Tstg	°C	-65 ~ + 175

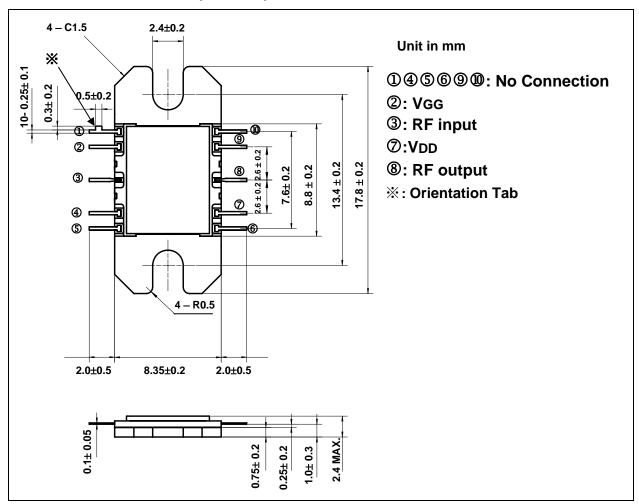
RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Operating Frequency	f		GHz	5.8		7.2
Output Power at 1dB Gain	P1dB		dBm	32.0	34.0	
Compression Point						
Power Gain at 1dB Gain	G1dB	VDD= 10V	dB	27.0	29.0	_
Compression Point		VGG= -5V				
Gain Flatness	ΔG		dB		_	±2.0
Drain Current	IDD		Α		1.2	1.6
Input VSWR	VSWRin				2.0	3.0
3 rd Order Intermodulation	IM ₃	Po (S.C.L.)=22.0 dBm	dBc	-42	-45	
Distortion						

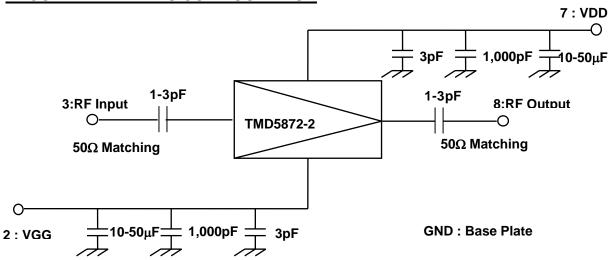
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The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

PACKAGE OUTLINE (2-9E1F)



RECOMMENDED BIAS CONFIGURATION



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C. Flanges of devices should be attached using screws and washers. Recommended torque is 0.18-0.20 N·m.